

Effect of ultrasonic treatment on the defect structure of the Si-SiO₂ system

Kropman, Daniel; Seeman, Viktor; Dolgov, Sergei; Medvids, Arturs Physica Status Solidi (C) Current Topics in Solid State Physics 2016 / p. 793 - 797 <https://doi.org/10.1002/pssc.201600052> [Journal metrics at Scopus](#) [Article at Scopus](#) [Article at WOS](#)

Interaction of point defects with impurities in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Käner, Tiit; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos; Misiuk, Andrzej Solid state phenomena 2011 / p. 263-266 <https://www.sciencedirect.com/science/article/pii/S0040609009014564>

Interaction of point defects with impurities in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Käner, Tiit; Dolgov, Sergei; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos Physica status solidi (c) 2011 / p. 694-696 : ill <https://www.sciencedirect.com/science/article/pii/S0040609009014564>

Understanding and control of stress at Si-SiO₂ interface

Kropman, Daniel; Seeman, Viktor; Medvids, Arturs; Onufrijevs, Pavels; Vitusevich, Svetlana; **Mikli, Valdek** Key engineering materials 2020 / p. 291–296 <https://doi.org/10.4028/www.scientific.net/KEM.850.291> [Journal metrics at Scopus](#) [Article at Scopus](#)